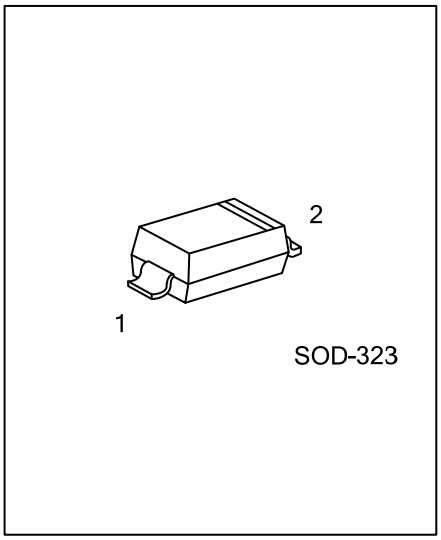
SD103AWS

DIODE

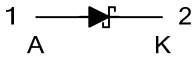
SCHOTTKY BARRIER SWITCHING DIODE



■ FEATURES

* Low Forward Voltage Drop
* Fast Switching
* Negligible Reverse Recovery Time
* Low Reverse Capacitance
* Designed for Surface Mount Application
* PN Junction Guard Ring for Transient and ESD Protection

■ SYMBOL

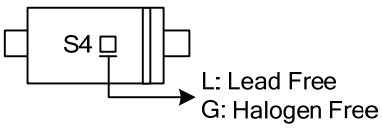


■ ORDERING INFORMATION

Order Number		Package	Pin Assignment		Packing
Lead Free	Halogen Free		1	2	
SD103AWSL-CB2-R	SD103AWSG-CB2-R	SOD-323	A	K	Tape Reel

SD103AWSL-CB2-R (1) Packing Type (2) Package Type (3) Lead Plating	(1) R: Tape Reel (2) CB2: SOD-323 (3) L: Lead Free, G: Halogen Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (Single Diode @T_A=25°C)

PARAMETER SYMBOL		RATINGS	UNIT
Maximum repetitive Peak Reverse Voltage	V_{RRM}	40	V
Maximum DC Blocking Voltage	V_R 40		V
Working Peak Reverse Voltage	V_{RWM}	40	V
Maximum RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Forward Continuous Current	I_{FM} 350		mA
Non-Repetitive Peak Forward Current at $t_P \leq 1.0s$	I_{FSM} 1.5		A
Power Dissipation	P_D	400	mW
Storage Temperature	T_{STG}	-65~+125	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Thermal Resistance Junction to Ambient	θ_{JA}	300	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A=25°C)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage Drop	V_F	I_F=20mA			0.37	V
		I_F=200mA			0.60	V
Reverse Breakdown Voltage	BV_R	I_R=10μA	40			V
Peak Reverse Leakage Current	I_{RM}	V_R=30V			5.0	μA
Typical Reverse Recovery Time	t_{RR}	I_F=I_R= 50~200mA, R_L=100Ω recover to 0.1x I_R	10			ns
Typical Junction Capacitance	C_T	V_R=0V, f=1.0MHz		50		pF

■ TYPICAL CHARACTERISTICS